

Amendments

In the Title:

Please delete the current title and insert "Method For Preventing Out-Diffusion of Impurities Implanted in Source/Drain Regions When Forming Transistor of Semiconductor Device".

In the Specification:

On pg. 1, line 3, please delete the heading "BACKTROUND OF THE IVNENTION" and insert new heading "BACKGROUND OF THE INVENTION".

On page 7, the second paragraph, starting on line 12, please amend as indicated:

The process of implanting the impurities 23 is preferably performed using a single-type equipment without wafer tilt and rotation, or with wafer tilt of 1° and under bi-rotation or ~~quadruple-rotation~~ quadruple-rotation configuration. In a case of bi-rotation, ion-implant process is performed twice using 1/2 of the entire dose. In a case of a ~~quadruple-rotation~~ quadruple-rotation, ion-implant process is performed four times using 1/4 of the entire dose.